

2.5V Drive Nch MOS FET

RJK005N03

●Structure

Silicon N-channel MOS FET

●Features

- 1) Low On-resistance.
- 2) Low voltage drive (2.5V drive).

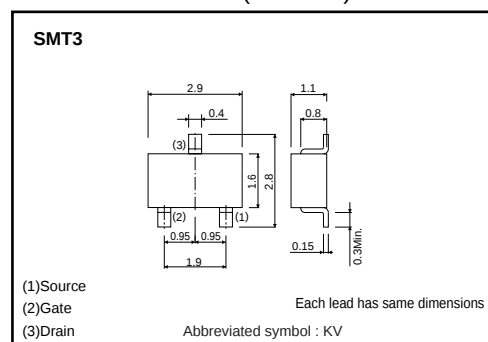
●Applications

Switching

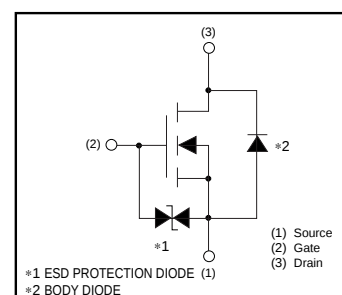
●Packaging specifications and h_{FE}

Type	Package	Taping
	Code	T146
	Basic ordering unit (pieces)	3000
RJK005N03		○

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings ($T_a=25^{\circ}\text{C}$)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DS}	30	V
Gate-source voltage		V_{GS}	± 12	V
Drain current	Continuous	I_D	± 500	mA
	Pulsed	I_{DP} *1	± 2.0	A
Source current (Body Diode)	Continuous	I_S	200	mA
	Pulsed	I_{SP} *1	800	mA
Total power dissipation		P_D *2	200	mW
Channel temperature		T_{ch}	150	$^{\circ}\text{C}$
Range of storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$

*1 $P_w \leq 10\mu\text{s}$, Duty cycles $\leq 1\%$

*2 Each terminal mounted on a recommended land

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	625	$^{\circ}\text{C/W}$

* Each terminal mounted on a recommended land

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	—	—	±10	μA	$V_{GS}=\pm 12V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D=1mA$, $V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS}=30V$, $V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.8	—	1.5	V	$V_{DS}=10V$, $I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	—	400	580	mΩ	$I_D=500mA$, $V_{GS}=4.5V$
		—	420	600	mΩ	$I_D=500mA$, $V_{GS}=4V$
		—	650	940	mΩ	$I_D=500mA$, $V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	0.5	—	—	S	$V_{DS}=10V$, $I_D=500mA$
Input capacitance	C_{iss}	—	60	—	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	—	24	—	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	—	12	—	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	—	9	—	ns	$V_{DD}\doteq 15V$
Rise time	t_r *	—	11	—	ns	$I_D=250mA$
Turn-off delay time	$t_{d(off)}$ *	—	16	—	ns	$V_{GS}=4V$
Fall time	t_f *	—	31	—	ns	$R_L=60\Omega$
Total gate charge	Q_g *	—	2.0	4.0	nC	$V_{DD}\doteq 24V$
Gate-source charge	Q_{gs} *	—	0.6	—	nC	$V_{GS}=4V$
Gate-drain charge	Q_{gd} *	—	0.7	—	nC	$I_D=500mA$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	—	—	1.2	V	$I_S=500mA$, $V_{GS}=0V$

*Pulsed

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

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moschip.ru_9